

What is claimed is:

1. (Amended) A semiconductor light emitting device comprising:

a substrate, and

a light emitting layer forming portion disposed on said substrate so that an active layer that emits light by electric current injection is sandwiched between n-type and p-type cladding layers made of materials having a larger band gap than said active layer,

wherein said active layer is made of a ZnO-based oxide compound semiconductor containing at least one of Cd and Zn.

5. (Amended) A semiconductor light emitting device comprising:

an active layer that emits light by electric current injection, and

cladding layers made of materials having a larger band gap than said active layer, said cladding layers sandwiching said active layer from both sides thereof,

wherein said cladding layers are made of ZnO-based oxide compound semiconductor containing Zn or Mg and Zn.

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40. (Amended) A method of manufacturing a semiconductor light emitting device in which a light emitting layer forming portion is epitaxially grown by an MOCVD method, said light emitting layer forming portion being constituted so that an active layer made of a ZnO-based oxide compound semiconductor is sandwiched between n-type and p-type layers made of ZnO-based oxide compound semiconductor,

wherein said p-type layer is formed by alternately repeating a step of growing a thin film of compound semiconductor layer by introducing a reaction gas for said p-type layer into a growth apparatus and a step of carrying out a doping process by introducing a p-type dopant gas.

41. (Amended) A method of growing a p-type compound semiconductor by vapor deposition in which a p-type compound semiconductor layer is epitaxially grown by an MOCVD method,

wherein said p-type compound semiconductor layer is formed by alternately repeating a step of growing a thin film of compound semiconductor layer by introducing a reaction gas for said p-type compound semiconductor layer into a growth apparatus; a step of purging said reaction gas for growing said thin film after the step of growing said thin film of compound semiconductor layer; and a step of carrying out a doping process by introducing a p-type dopant gas.

42. (Amended) The growth method of claim 41, wherein only an organic metal material is used as the reaction gas for growing said semiconductor layer.

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